

What is claimed is:

1. A manufacturing method for a semiconductor device comprising:

5 a hole portion formation step for forming hole portions whose entire width is substantially identical to the width of the opening portion in a part of the active surface side of the substrate on which electronic components are formed;

a curved surface formation step for curving the bottom surface of the hole portion while maintaining the width of the bottom surface in the hole portions substantially identical to the width of the opening portion;

10 a connecting terminal formation step for forming connecting terminals that serve as the external electrodes of the electronic circuits by burying metal in the hole portions; and

an exposure step for exposing a part of the connecting terminals by carrying out processing on the back surface of the substrate.

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2. A manufacturing method for a semiconductor device according to claim 1,

wherein the curved surface formation step is a step in which the bottom surface of the hole portion is formed into an approximately semispherical shape by isotropic etching.

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3. A manufacturing method for a semiconductor device according to claim 1,

wherein the exposure step is a step in which a part of the connecting terminals is exposed without changing the shape of the connecting terminals.

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4. A manufacturing method for a semiconductor device according to claim 1,

comprising an insulating film formation step of forming an insulating film on the inner wall and the bottom surface of the hole portions between the curved surface formation step and the connecting terminal formation step, and further

the exposure step comprising:

5           a first etching step for etching the back surface of the substrate until the thickness of the substrate is approximately slightly thicker than the burying depth of the connecting terminals;

          a second etching step for exposing the insulating film formed in the hole portions by etching the back surface of the substrate at an etching rate that is lower than  
10   the etching rate in the first etching step; and

          a third etching step for exposing the connecting terminals by etching at least a part of the exposed insulating film.

5. A manufacturing method for a semiconductor device comprising:

15           a concavo-convex shape formation step for forming a concavo-convex shape on a part of the active surface side of the substrate on which the electronic circuits are formed;

          a hole formation step for forming hole portions by etching the area in which the concavo-convex shape has been formed, whose entire width is substantially equal to the  
20   width of the area on which the concavo-convex shape has been formed and whose bottom surface has a shape substantially identical to the concavo-convex shape;

          a connecting terminal formation step for forming the connecting terminals that serve as the external electrodes of the electronic circuits by burying metal in the hole portions; and

25           an exposure step for exposing a part of the connecting terminals by carrying out

processing of the back surface of the substrate.

6. A manufacturing method for a semiconductor device according to claim 5,  
wherein the exposure step is a step in which a part of the connecting terminals is

5 exposed without changing the shape of the connecting terminals.

7. A manufacturing method for a semiconductor device according to claim 5  
comprising an insulating film formation step for forming an insulating film on the inner  
wall and the bottom surface of the hole portions between the hole formation step and the

10 connecting terminal formation step, and further

the exposure step comprising:

a first etching step for etching the back surface of the substrate until the  
thickness of the substrate is approximately slightly thicker than the burying depth of the  
connecting terminals;

15 a second etching step for exposing the insulating film formed in the hole  
portions by etching the back surface of the substrate at an etching rate that is lower than  
the etching rate in the first etching step; and

a third etching step for exposing the connecting terminals by etching at least a  
part of the exposed insulating film.

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8. A manufacturing method for a semiconductor device comprising:

a mask formation step for forming a mask having a plurality of holes in the hole  
formation area set in a part of the active surface side of the substrate on which the  
electronic circuits are formed;

25 a concavo-convex shape hole formation step for forming hole portions whose

entire width is substantially identical to the width of the hole formation area and whose bottom surface has a concavo-convex shape by etching the substrate through each of the holes formed in the mask using an etching method in which the holes widen slightly in the surface direction of the substrate;

5           a connecting terminal formation step for forming connecting terminals that serve as the external electrodes for the electronic circuits by burying metal in the hole portions ; and

          an exposure step for exposing a part of the connecting terminals by carrying out processing on the back surface of the substrate.

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9. A manufacturing method for a semiconductor device according to claim 8,

          wherein the exposure step is a step in which a part of the connecting terminals is exposed without changing the shape of the connecting terminals.

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10. A manufacturing method for a semiconductor device according to claim 8 comprising an insulating film formation step for forming an insulating film on the inner wall and the bottom surface of the hole portions between the concavo-convex hole formation step and the connecting terminal formation step, and further

          the exposure step comprising:

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          a first etching step for etching the back surface of the substrate until the thickness of the substrate is approximately slightly thicker than the burying depth of the connecting terminals;

          a second etching step for exposing the insulating film formed in the hole portions by etching the back surface of the substrate at an etching rate that is lower than

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          the etching rate in the first etching step; and

a third etching step for exposing the connecting terminals by etching at least a part of the exposed insulating film.

11. A manufacturing method for a semiconductor device comprising:

5 a dicing step for dicing the semiconductor device formed by the manufacturing method for a semiconductor device according to claim 1 into individual semiconductor chips;

a stacking step for stacking an identical type of the semiconductor chips or different types of the semiconductor chips; and

10 a bonding step for bonding together the connecting terminals formed on the stacked semiconductor chips.

12. A manufacturing method for a semiconductor device comprising:

15 a dicing step for dicing the semiconductor device formed by the manufacturing method for a semiconductor device according to claim 1 into individual semiconductor chips;

a mounting step for mounting one or a plurality of the identical type of semiconductor chips or the different types of semiconductor chips on the substrate on which the connecting portion is formed; and

20 a bonding step for bonding together the connecting terminals formed on the stacked semiconductor chips or bonding the connecting portion and the connecting terminals.

13. A manufacturing method for a semiconductor device comprising:

25 a dicing step for dicing the semiconductor device formed by the manufacturing

method for a semiconductor device according to claim 5 into individual semiconductor chips;

a stacking step for stacking an identical type of the semiconductor chips or different types of the semiconductor chips; and

5 a bonding step for bonding together the connecting terminals formed on the stacked semiconductor chips.

14. A manufacturing method for a semiconductor device comprising:

a dicing step dicing the semiconductor device formed by the manufacturing  
10 method for a semiconductor device according to claim 5 into individual semiconductor chips;

a mounting step for mounting one or a plurality of the identical type of semiconductor chips or the different types of semiconductor chips on the substrate on which the connecting portion is formed; and

15 a bonding step for bonding together the connecting terminals formed on the stacked semiconductor chips or bonding the connecting portion and the connecting terminals.

15. A manufacturing method for a semiconductor device comprising:

20 a dicing step for dicing the semiconductor device formed by the manufacturing method for a semiconductor device according to claim 8 into individual semiconductor chips;

a stacking step for stacking an identical type of the semiconductor chips or different types of the semiconductor chips; and

25 a bonding step for bonding together the connecting terminals formed on the

stacked semiconductor chips.

16. A manufacturing method for a semiconductor device comprising:

5 a dicing step for dicing the semiconductor device formed by the manufacturing method for a semiconductor device according to claim 8 into individual semiconductor chips;

a mounting step for mounting one or a plurality of the identical type of semiconductor chips or the different types of semiconductor chips on the substrate on which the connecting portion is formed; and

10 a bonding step for bonding together the connecting terminals formed on the stacked semiconductor chips or bonding the connecting portion and the connecting terminals.

17. A semiconductor device manufactured by the manufacturing method for a  
15 semiconductor device in claim 1.

18. A semiconductor device manufactured by the manufacturing method for a semiconductor device in claim 5.

20 19. A semiconductor device manufactured by the manufacturing method for a semiconductor device in claim 8.

20. A semiconductor device comprising:

a thinned substrate having an active surface on which electronic circuits are  
25 formed; and

connecting terminals that serve as the external electrodes for the electronic circuits formed by passing through the substrate from the active surface side to the back surface side; and wherein

the distal ends of the connecting terminals in the back surface side of the substrate have a curved surface shape.

21. A semiconductor device according to claim 20,

wherein the distal ends of the connecting terminals have an approximately semispherical curved surface shape.

22. A semiconductor device according to claim 20,

wherein the distal ends of the connecting terminals have a concavo-convex shape.

23. A semiconductor device wherein the semiconductor device according to claim 20 are stacked in plurality and the connecting terminals are bonded together.

24. A semiconductor device comprising:

a mounting substrate on which a connection part is formed; and

one or a plurality of a semiconductor device according to claim 17 mounted on the mounting substrate; and wherein

the connecting terminals are bonded together or the connecting portion and the connecting terminals are bonded together.

25. A semiconductor device comprising:



a mounting substrate on which a connection part is formed; and  
one or a plurality of a semiconductor device according to claim 18 mounted on  
the mounting substrate; and wherein  
the connecting terminals are bonded together or the connecting portion and the  
5 connecting terminals are bonded together.

26. A semiconductor device comprising:

a mounting substrate on which a connection part is formed; and  
one or a plurality of a semiconductor device according to claim 19 mounted on  
10 the mounting substrate; and wherein  
the connecting terminals are bonded together or the connecting portion and the  
connecting terminals are bonded together.

27. A semiconductor device comprising:

15 a mounting substrate on which a connection part is formed; and  
one or a plurality of a semiconductor device according to claim 20 mounted on  
the mounting substrate; and wherein  
the connecting terminals are bonded together or the connecting portion and the  
connecting terminals are bonded together.

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28. An electronic apparatus comprising the semiconductor device according to claim  
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29. An electronic apparatus comprising the semiconductor device according to claim  
25 18.

30. An electronic apparatus comprising the semiconductor device according to claim 19.
- 5 31. An electronic apparatus comprising the semiconductor device according to claim 20.